

**Erratum: Energetic, vibrational, and electronic properties of silicon
using a nonorthogonal tight-binding model
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A typographical error was found in the table of parameters for the sp^3d^5 basis tight-binding model for silicon. The parameters affected govern the $H_{sd\sigma}$ and $H_{pd\sigma}$ Hamiltonian matrix elements. The correct parameters are listed in Table I. The simulation results in the paper were computed using the correct parameters, and are therefore not affected by this error. The correct parameters are also available via the World Wide Web at <http://cst-www.nrl.navy.mil/bind/si.html>.

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TABLE I. Corrected parameters for the sp^3d^5 basis tight-binding model.

Interaction	Hamiltonian Matrix Parameters			
	a (Ry)	b (Ry/a.u.)	c (Ry/a.u. ²)	g (a.u. ^{-1/2})
$H_{sd\sigma}$	-7571.4416	223.5445	701.2195	1.6234
$H_{pd\sigma}$	-1808.7340	-346.9465	-77.6365	1.6294